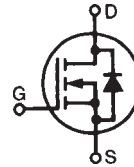


PolarHV™ Power MOSFET

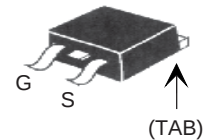
N-Channel Enhancement Mode
Avalanche Rated

IXTA 5N50P
IXTP 5N50P
IXTV 5N50P
IXTY 5N50P

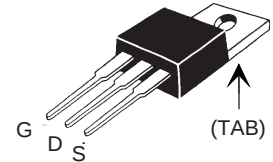
$$\begin{aligned} V_{DSS} &= 500 \text{ V} \\ I_{D25} &= 4.8 \text{ A} \\ R_{DS(on)} &\leq 1.4 \Omega \end{aligned}$$



TO-263 (IXTA)

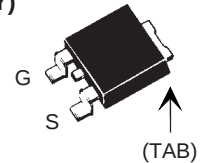


TO-220 (IXTP)



TO-252 (IXTU)

TO-252 (IXTY)



G = Gate
S = Source

D = Drain
TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	500	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	4.8	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	10	A
I_{AR}	$T_C = 25^\circ\text{C}$	5	A
E_{AR}	$T_C = 25^\circ\text{C}$	20	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	250	mJ
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 30 \Omega$	10	V/ns
P_D	$T_C = 25^\circ\text{C}$	89	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
T_{SOLD}	Plastic body for 10 s	260	$^\circ\text{C}$
M_d	Mounting torque (TO-220)	1.13/10	Nm/lb.in.
Weight	TO-220	4	g
	TO-263	3	g
	TO-252	0.8	g

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 50 \mu\text{A}$	3.0		5.5 V
I_{GSS}	$V_{GS} = \pm 30 \text{ V}$, $V_{DS} = 0 \text{ V}$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$			5 μA
	$V_{GS} = 0 \text{ V}$, $T_J = 125^\circ\text{C}$			50 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$			1.4 Ω

Features

- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect

Advantages

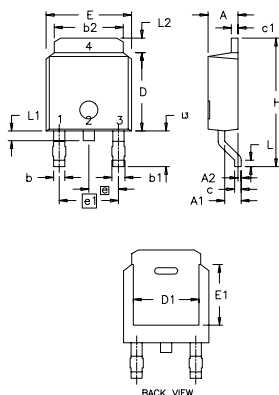
- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{ V}$; $I_D = 0.5 I_{D25}$, pulse test	3.0	4.7	S
C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$		620	pF
C_{oss}			72	pF
C_{rss}			6.3	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 V_{DSS}$, $I_D = 0.5 I_{D25}$ $R_G = 30\ \Omega$ (External)		22	ns
t_r			26	ns
$t_{d(off)}$			65	ns
t_f			24	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 V_{DSS}$, $I_D = 0.5 I_{D25}$		12.6	nC
Q_{gs}			4.3	nC
Q_{gd}			5.0	nC
R_{thJC}	(TO-220)			1.4°C/W
R_{thCS}			0.25	$^\circ\text{C/W}$

Source-Drain Diode		Characteristic Values ($T_J = 25^\circ\text{C}$ unless otherwise specified)		
Symbol	Test Conditions	Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{ V}$			5 A
I_{SM}	Repetitive			15 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{ V}$, Pulse test			1.5 V
t_{rr}	$I_F = 5\text{ A}$, $-di/dt = 100\text{ A}/\mu\text{s}$, $V_R = 100\text{ V}$, $V_{GS} = 0\text{ V}$		400	ns

Note 1: Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$

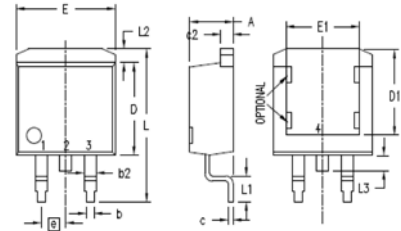
TO-252 (IXTY) Outline



Pins: 1 - Gate
3 - Source
2,4 - Drain

Dim.	Millimeter Min. Max.	Inches Min. Max.
A	2.19 2.38	0.086 0.094
A1	0.89 1.14	0.035 0.045
A2	0 0.13	0 0.005
b	0.64 0.89	0.025 0.035
b1	0.76 1.14	0.030 0.045
b2	5.21 5.46	0.205 0.215
c	0.46 0.58	0.018 0.023
c1	0.46 0.58	0.018 0.023
D	5.97 6.22	0.235 0.245
D1	4.32 5.21	0.170 0.205
E	6.35 6.73	0.250 0.265
E1	4.32 5.21	0.170 0.205
e	2.28 BSC	0.090 BSC
e1	4.57 BSC	0.180 BSC
H	9.40 10.42	0.370 0.410
L	0.51 1.02	0.020 0.040
L1	0.64 1.02	0.025 0.040
L2	0.89 1.27	0.035 0.050
L3	2.54 2.92	0.100 0.115

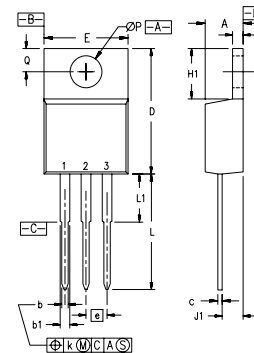
TO-263 (IXTA) Outline



1. GATE (COLLECTOR)
2. DRAIN (COLLECTOR)
3. SOURCE (EMITTER)
4. DRAIN (COLLECTOR) BOTTOM SIDE

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

TO-220 (IXTP) Outline



Pins: 1 - Gate 2 - Drain
3 - Source 4 - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2

Fig. 1. Output Characteristics
@ 25°C

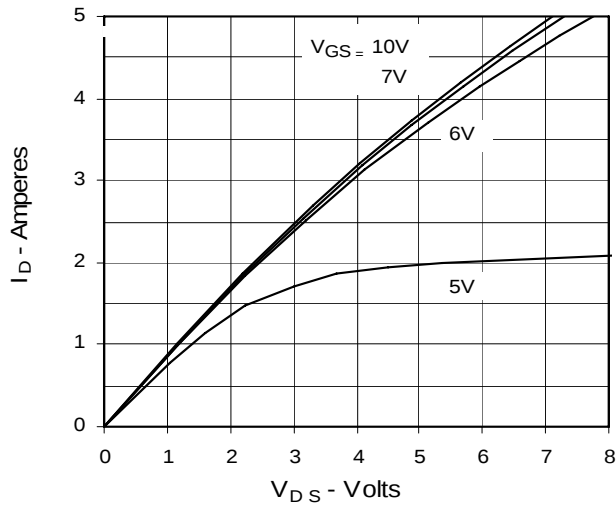


Fig. 2. Extended Output Characteristics
@ 25°C

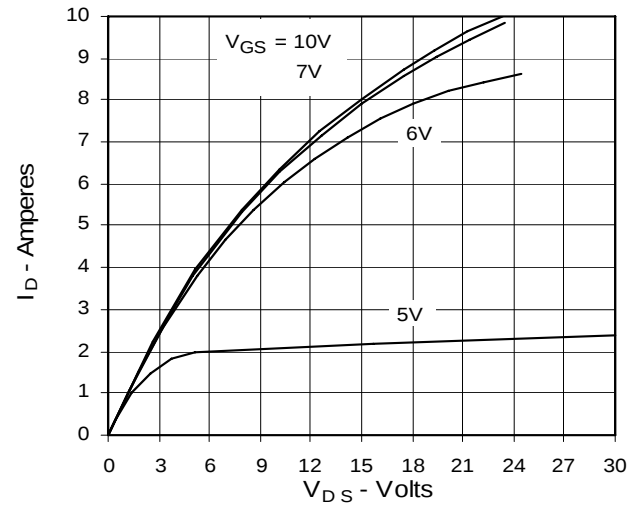


Fig. 3. Output Characteristics
@ 125°C

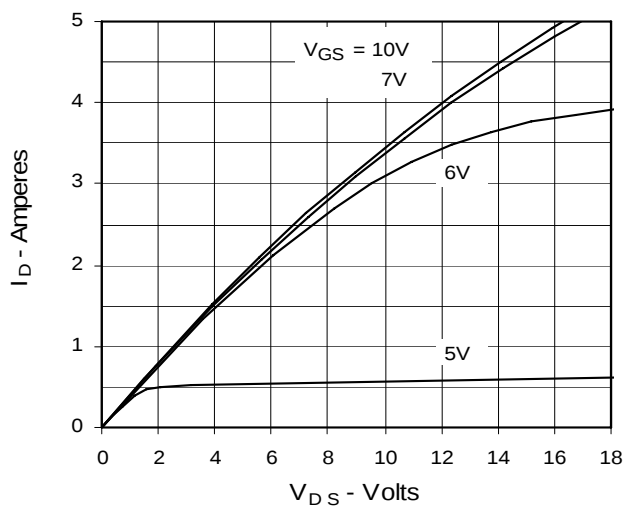


Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Junction Temperature

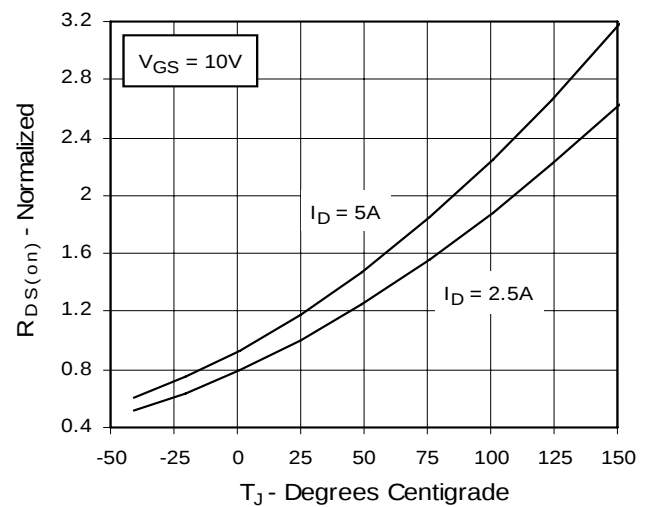


Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. I_D

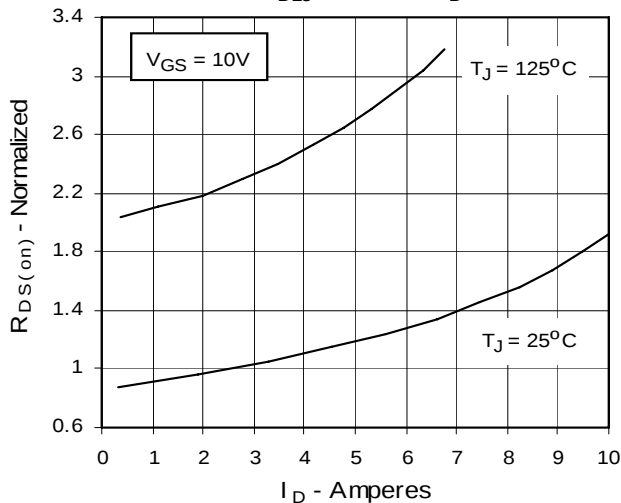


Fig. 6. Drain Current vs. Case Temperature

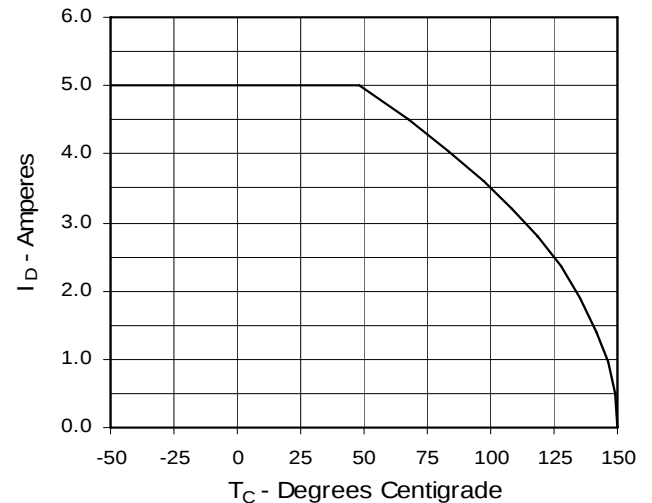


Fig. 7. Input Admittance

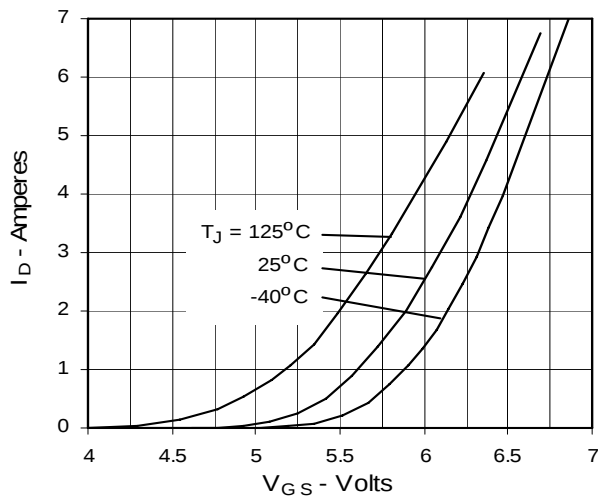


Fig. 8. Transconductance

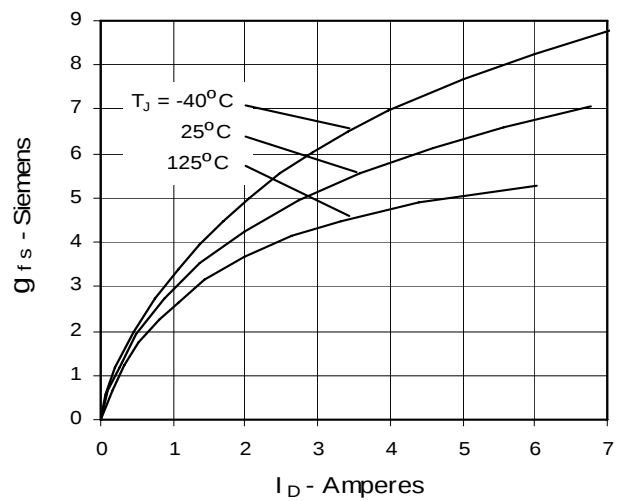


Fig. 9. Source Current vs. Source-To-Drain Voltage

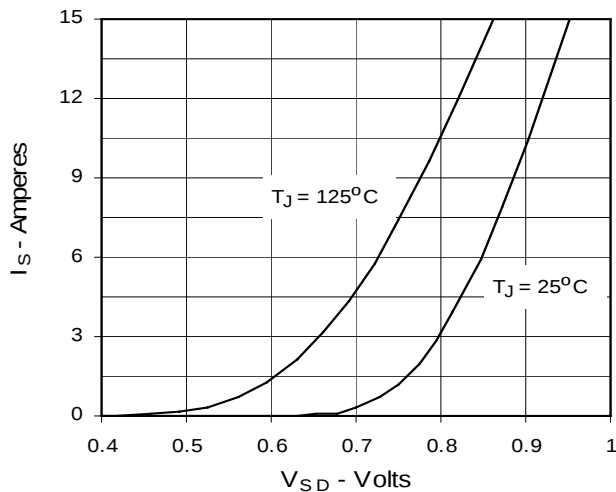


Fig. 10. Gate Charge

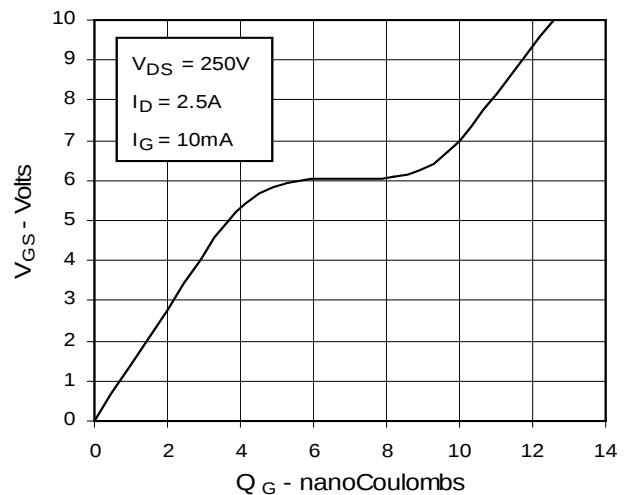


Fig. 11. Capacitance

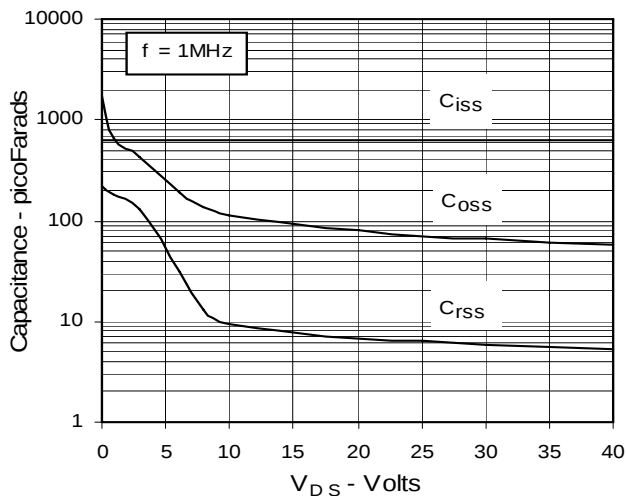


Fig. 12. Forward-Bias Safe Operating Area

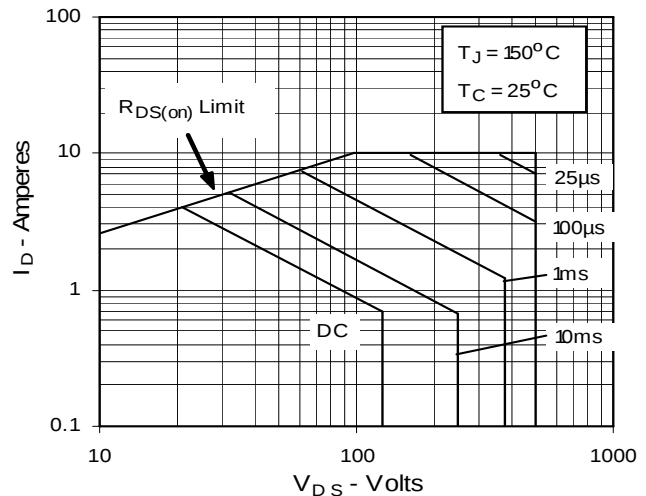


Fig. 13. Maximum Transient Thermal Resistance

